

DSS5140U

40V PNP LOW SATURATION TRANSISTOR IN SOT323

Features

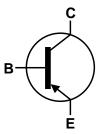
- BV_{CEO} > -40V
- I_C = -1A Continuous Collector Current
- I_{CM} = -2A Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -500 \text{mV} @ I_C = -1 \text{A}$
- Ultra-Small Surface Mount Package
- Complementary NPN Type: DSS4140U
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

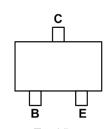
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)







Device Symbol



Top View Pin-Out

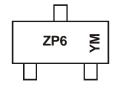
Ordering Information (Note 4)

Device	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
DSS5140U-7	AEC-Q101	ZP6	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZP6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2010	2	2011	2012	2013	2014	2015	2016	6 20	17 2	2018	2019	2020
Code	Х		Υ	Z	Α	В	С	D	Е		F	G	Н
Month	ı	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	Ic	-1	Α
Peak Pulse Collector Current	I _{CM}	-2	Α
Peak Base Current	I _{BM}	-1	Α

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	0	400	mW	
Power Dissipation	(Note 6)	P _D	500	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	0	313	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	250	C/VV	
Thermal Resistance, Junction to Leads	$R_{ heta JL}$	350	°C/W		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

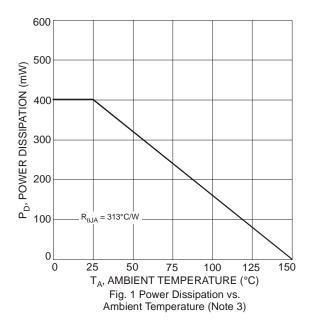
 6. Same as Note 5, except the collector lead is on a 25mm x 25mm loz copper.

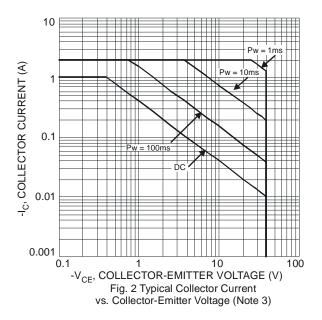
 7. Thermal resistance from junction to solder-point (at the end of the leads).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





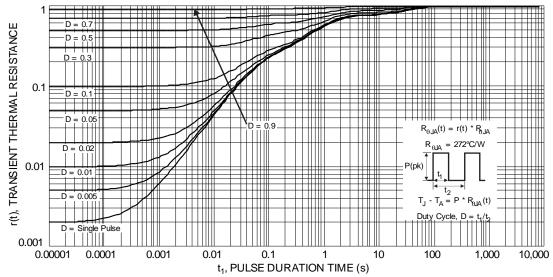


Fig. 3 Transient Thermal Response (Note 3)



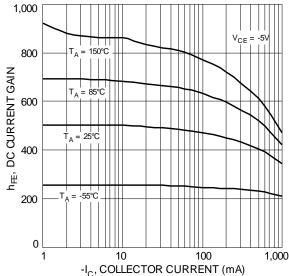
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

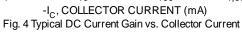
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_		V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	_		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_		٧	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -40V, I _E = 0
	1000			-50	μA	$V_{CB} = -40V, I_E = 0, T_J = +150$ °C
Collector Cutoff Current	I _{CES}		_	-100	nA	$V_{CE} = -40V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -5V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)	,					
		300	_	_		$V_{CE} = -5V$, $I_C = -1mA$
DC Current Gain	h _{FE}	300	_	800	_	$V_{CE} = -5V, I_{C} = -100mA$
Do Garrotti Garr	''FE	250	_	_		$V_{CE} = -5V, I_{C} = -500mA$
		160	_			$V_{CE} = -5V$, $I_C = 1A$
		_	_	-200	mV	$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-250		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
		_	_	-500		$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	_	500	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	-1.1	V	$I_C = -1A$, $I_B = -50mA$
Base-Emitter Turn On Voltage	V _{BE(ON)}	_	_	-1	V	$V_{CE} = -5V, I_{C} = -1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	13		рF	$V_{CB} = -10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f⊤	150	_		MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	_	60	_	ns	
Delay Time	t _d		25		ns	
Rise Time	t _r		35		ns	V _{CC} = -10V
Turn-Off Time	t _{off}	_	250		ns	$I_C = -0.5A$, $I_{B1} = -I_{B2} = -25mA$
Storage Time	ts	_	220		ns	
Fall Time	t _f	_	30	_	ns	

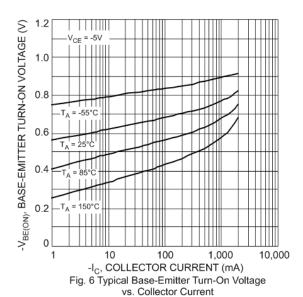
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

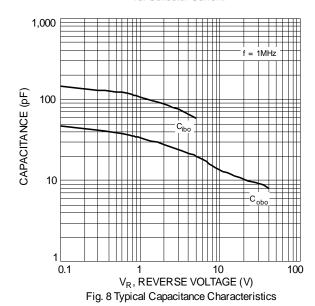


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









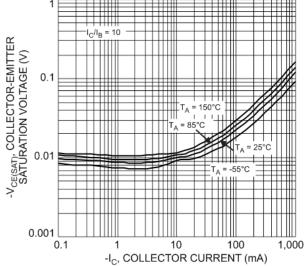


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

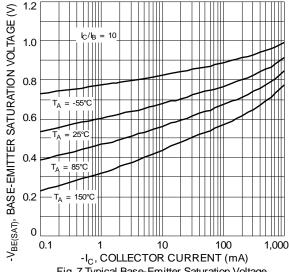
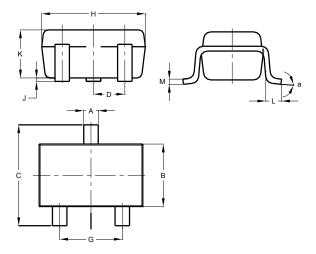


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

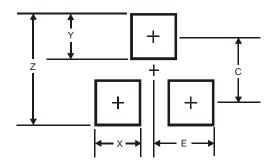
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	0.	.650 BS	C			
F	0.375	0.475	0.425			
G	1.20	1.40	1.30			
Н	1.80	2.20	2.15			
J	0.00	0.10	0.05			
K	0.90	1.00	0.95			
L	0.25	0.40	0.30			
М	0.10	0.18	0.11			
а	8°C					
All I	Dimens	ions in	mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	SOT323
Z	2.8
Х	0.7
Υ	0.9
С	1.9
Е	1.0



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